

Description

The AP3N9R5MT uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

 $V_{DS} = 30V I_{D} = 50A$

 $R_{DS(ON)}$ < 8.5m Ω V_{GS}=10V

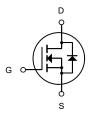
Application

Battery protection

Load switch

Uninterruptible power supply

DFN5X6-8L (PMPAK-8(5x6))



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
AP3N9R5MT	DFN5X6-8L(PMPAK-8(5x6))	HXY MOSFET	5000

Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units		
VDS	Drain-Source Voltage	30	V		
Vgs	Gate-Source Voltage	Gate-Source Voltage ±20			
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V	Continuous Drain Current, V _{GS} @ 10V 60			
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 10V	38	Α		
Ідм	Pulsed Drain Current ¹	Pulsed Drain Current ¹ 200			
EAS	Single Pulse Avalanche Energy ²	36	mJ		
las	Avalanche Current	50	Α		
P _D @T _C =25°C	Total Power Dissipation ⁴	31	W		
Тѕтс	Storage Temperature Range	-55 to 150	°C		
TJ	Operating Junction Temperature Range	-55 to 150	°C		
Reja	Thermal Resistance Junction-Ambient 62		°C/W		
Rелс	Thermal Resistance Junction-Case ³		°C/W		



Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Тур	Max	Units
BV _{DSS}	Drain-Sourtce Breakdown Voltage	V _{GS} =0V,I _D =250μA	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} =0V, V _{DS} =24V			1	μΑ
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0A			±100	nA
V _{GS(th)}	GATE-Source Threshold Voltage	V _{GS} =V _{DS} , I _D =250μA	1.2	1.5	2.5	V
R	Drain-Source On Resistance ⁴	V _{GS} =10V,I _D =30A 6.		6.5	8.5	
$R_{DS(ON)}$		V _{GS} =4.5V,I _D =15A		11	14	mΩ
G _{FS}	Forward Transconductance	V _{DS} =5V, I _D =30A		38		S
C _{iss}	Input Capacitance			1317	1844	pF
C _{oss}	Output Ca pacitance	$V_{DS} = 15V, V_{GS} = 0V,$ f = 1MHz		163	228	
C _{rss}	Reverse Transfer Capacitance	1-1101112		131	183	
t _{d(on)}	Turn-On Delay Time			4.6	9.2	ns
t _r	Rise Time	V _{DD} =15V,I _D =15A,		12.2	22	ns
t _{d(off)}	Turn-Off Delay Time	V_{GS} =15V, R_{G} =3.3 Ω		26.6	53	ns
t _f	Fall Time			8	16	ns
Q_g	Total Gate Charge			17.6	21	nC
Q_{gs}	Gate-Source Charge	V _{GS} =4.5V,		2:35	5.9	nC
Q_{gd}	Gate-Drain "Miller" Charge	V _{DS} =15V, I _D =15A		5.9	7.1	nC
V _{SD}	Source-Drain Diode Forward Voltage	V _{GS} =0V,I _S =1A			1	V
IS	Continuous Source Current	VG=VD=0V,			58	Α
ISM	Pulsed Source Current	Force Current			115	Α
trr	Reverse Recovery Time	IF=30A,		9.2		ns
Qrr	Reverse Recovery Charge	dI/dt=100A/¦ÌsTJ=25℃		2		nC

Notes:

- 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
- 2. E_{AS} condition: Starting T_J =25C, V_{DD} =15V, V_G =10V, R_G =25ohm, L=0.5mH, I_{AS} =14A
- 3. R_{0,JA} is measured with the device mounted on a 1inch² pad of 2oz copper FR4 PCB
- 4. Pulse Test: Pulse Width≤300µs, Duty Cycle≤0.5%.



Typical Characteristics

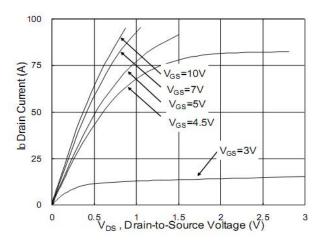


Fig.1 Typical Output Characteristics

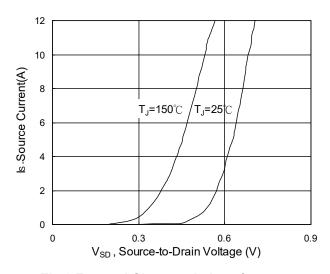


Fig.3 Forward Characteristics of reverse

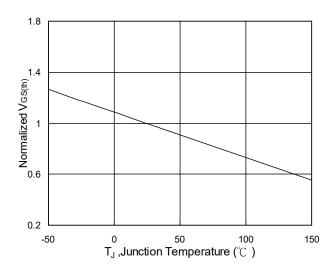


Fig.5 Normalized $V_{\text{GS(th)}}$ vs. T_{J}

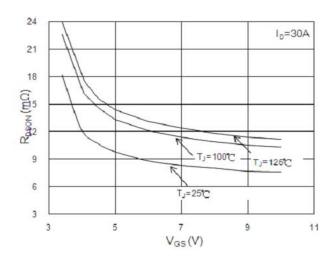


Fig.2 On-Resistance vs. Gate-Source

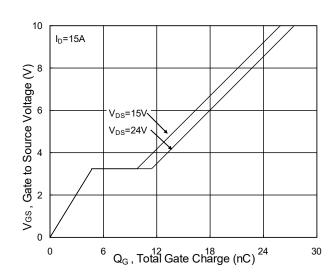


Fig.4 Gate-Charge Characteristics

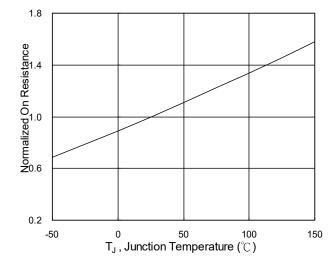
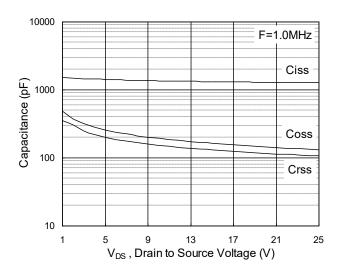


Fig.6 Normalized R_{DSON} vs. T_J





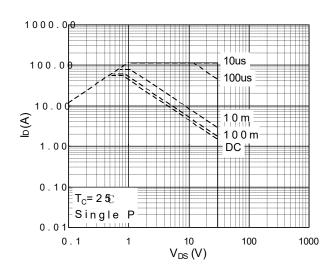
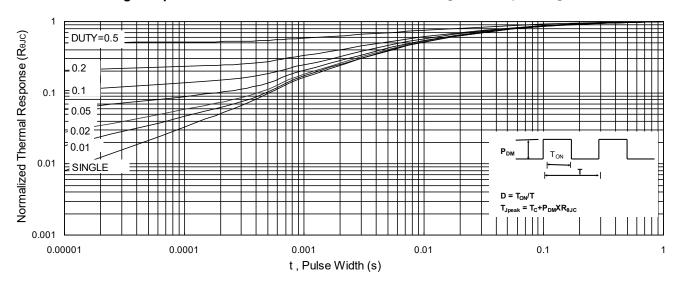
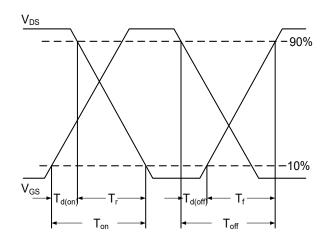


Fig.7 Capacitance

Fig.8 Safe Operating Area





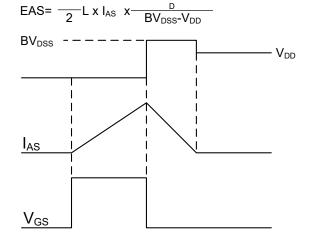
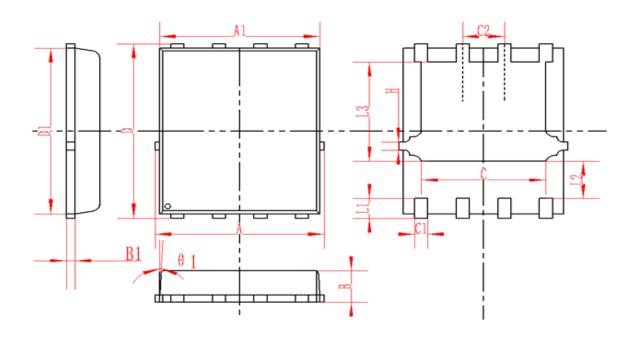


Fig.10 Switching Time Waveform



DFN5X6-8L(PMPAK -8(5x6)) Package Information



SYMBOL	MM		INCH			
	MIN	NOM	MAX	MIN	NOM	MAX
Α	5.3	5.5	5.7	0.208	0.216	0.224
A1	5.1	5.2	5.3	0.2	0.204	0.209
D	5.98	6	6.02	0.235	0.236	0.237
D1	5.85	6.05	6.25	0.23	0.238	0.246
В	0.85	0.95	1.05	0.033	0.037	0.041
B1	0.254REF		0.010REF			
С	3.95	4	4.05	0.156	0.157	0.159
C1	0.35	0.4	0.45	0.014	0.016	0.018
C2		1.27TYP			0.5TYP	
θ1	8°	10°	12°	8°	10°	12°
L1	0.63	0.64	0.65	0.025	0.025	0.026
L2	1.2	1.3	1.4	0.047	0.051	0.055
L3	3.415	3.42	3.425	0.134	0.135	0.135
Н	0.24	0.25	0.26	0.009	0.010	0.010

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